

1a

(19)



JAPANESE PATENT OFFICE

BEST AVAILABLE COPY

PATENT ABSTRACTS OF JAPAN

(11) Publication number: 02051836 A

(43) Date of publication of application: 21.02.90

(51) Int. Cl.

H01J 37/244

G01R 31/00

H01J 37/05

H01J 37/317

H01L 21/265

(21) Application number: 63201251

(71) Applicant: NEC KYUSHU LTD

(22) Date of filing: 12.08.88

(72) Inventor: DAIHO YOSHIYUKI

(54) ION IMPLANTER

COPYRIGHT: (C)1990,JPO&Japio

(57) Abstract:

PURPOSE: To detect the degree of squeezing an ion beam and prevent the electrostatic breakdown on a wafer due to charge-up and the nonuniform ion implantation in the face by constituting a flag Faraday with a main Faraday and a center Faraday.

CONSTITUTION: An ion implanter has a flag Faraday 1 shielding an ion beam and measuring the beam current when no ion is implanted, the flag Faraday 1 is constituted of a box-shaped main Faraday 1A having the first opening section 2A provided on the first side wall 9A to introduce the ion beam and the second opening section 2B provided on the second side wall 9B facing the first side wall 9A and smaller than the first opening section 2A and a center Faraday 18 measuring the beam current of the ion beam incoming through the second opening section 2B provided on the outer side face of the second side wall 9B via an insulator 7. The degree of squeezing the ion beam can be thereby detected, the electrostatic breakdown or the like on a wafer can be prevented.

